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**Accession number:** 20170503300176**Title:** Growth of single-phase wurtzite BAlN with 7.2%-B contents**Authors:** Li, Xiaohang<sup>1, 2</sup> ; Wang, Shuo<sup>3</sup>; Liu, Hanxiao<sup>3</sup>; Ponce, Fernando<sup>3</sup>; Detchprohm, Theeradetch<sup>1</sup>; Dupuis, Russell<sup>1</sup>**Author affiliation:** 1 School of Electrical and Computer Engineering, Georgia Institute of Technology, Atlanta; GA; 30332, United States

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